In the Claims:

- 1. (canceled)
- 2. (canceled)
- 3. (canceled)
- 4. (canceled)
- 5. (canceled)
- 6. (canceled)
- 7. (canceled)
- 8. (canceled)
- 9. (canceled)
- 10. (new) A material comprising epitaxial Ba_xSr_{1-x}TiO₃ formed as a layer on the C-plane of a sapphire substrate, wherein x has a value from 0 to 1.
- 11. (new) The material of Claim 10 wherein said layer is between about 100 and about 3000 nanometers thick.
- 12. (new) The material of Claim 10 wherein said layer is between about 300 and about 1000 nanometers thick.
- 13. (new) The material of Claim 10 wherein said Ba_xSr_{1-x}TiO₃ has a 111 orientation.
- 14. (new) The material of Claim 10 wherein said Ba_xSr_{1-x}TiO₃ is doped with an ion or ions that change its properties.
- 15. (new) The material of Claim 14 wherein said doping ions comprise cesium and bismuth.
- 16. (new) The material of claim 10 further comprising conductive electrodes for applying a bias or RF signal to the Ba_xSr_{1-x}TiO₃ layer.
- 17. (new) A material comprising epitaxial Ba_xSr_{1-x}TiO₃ formed as a layer on a sapphire substrate, wherein x has a value from 0.1 to 0.9.
- 18. (new) The material according to Claim 17 wherein x has a value from 0.3 to 0.7.
- 19. (new) The material according to Claim 17 wherein x has a value from 0.4 to 0.6.

- 20. (new) The material of Claim 17 wherein said layer is between about 100 and about 3000 nanometers thick.
- 21. (new) The material of Claim 17 wherein said layer is between about 300 and about 1000 nanometers thick.
- 22. (new) The material of Claim 17 wherein said Ba_xSr_{1-x}TiO₃ has a 111 orientation.
- 23. (new) The material of Claim 17 wherein said Ba_xSr_{1-x}TiO₃ is doped with an ion or ions that change its properties.
- 24. (new) The material of Claim 23 wherein said doping ions comprise cesium and bismuth.
- 25. (new) The material of Claim 17 further comprising conductive electrodes for applying a bias or RF signal to the Ba_xSr_{1-x}TiO₃ layer.